



August 2016

# FCB110N65F

## N-Channel SuperFET® II FRFET® MOSFET

650 V, 35 A, 110 mΩ

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 96\text{ m}\Omega$  (Typ.)
- Ultra Low Gate Charge (Typ.  $Q_g = 98\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 464\text{ pF}$ )
- 100% Avalanche Tested
- RoHS Compliant

### Applications

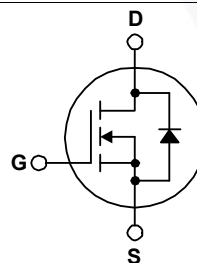
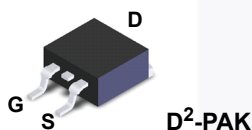
- Telecom/Server Power Supplies
- Solar Inverters
- Computing Power Supplies
- FPD TV Power/Lighting

### Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance.

SuperFET® II FRFET® MOSFET combines a faster and more rugged intrinsic body diode performance with fast switching, aimed at achieving better reliability and efficiency especially in resonant switching applications.

SuperFET® II FRFET® is very suitable for the switching power applications such as server/telecom power, Solar inverter, FPD TV power, computing power, lighting and industrial power applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCB110N65F	Unit
$V_{DSS}$	Drain to Source Voltage	650	V
$V_{GSS}$	Gate to Source Voltage	- DC	V
		- AC	
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	MOSFET dv/dt	(Note 3)	V/ns
	Peak Diode Recovery dv/dt		
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	W
		- Derate Above $25^\circ\text{C}$	$W/^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FCB110N65F	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> Pad of 2-oz copper), Max.	40	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Tape Width
FCB110N65F	FCB110N65F	D <sup>2</sup> -PAK	Tape and Reel	330 mm	24 mm	800 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	650	-	-	V
		$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_J = 150^\circ\text{C}$	700	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	0.72	-	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	110	-	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3.5\text{ mA}$	3	-	5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 17.5\text{ A}$	-	96	110	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 17.5\text{ A}$	-	30	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	3680	4895	pF
$C_{oss}$	Output Capacitance		-	110	145	pF
$C_{rss}$	Reverse Transfer Capacitance		-	0.65	-	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	65	-	pF
$C_{oss\text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	464	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 17.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	98	145	nC
$Q_{gs}$	Gate to Source Gate Charge		-	20	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	43	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	0.7	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 17.5\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$ (Note 4)	-	31	72	ns
$t_r$	Turn-On Rise Time		-	21	52	ns
$t_{d(off)}$	Turn-Off Delay Time		-	89	188	ns
$t_f$	Turn-Off Fall Time		-	5.7	21	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current	-	-	35	A	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current	-	-	100	A	
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 17.5 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 17.5 A,	-	133	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt = 100 A/μs	-	0.67	-	μC

#### Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2.  $I_{AS} = 8\text{ A}$ ,  $R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 17.5\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 380\text{ V}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

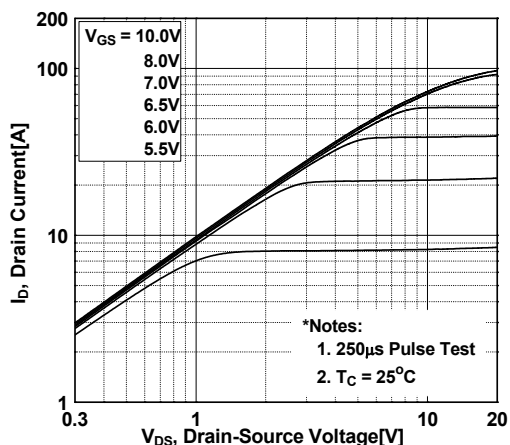


Figure 2. Transfer Characteristics

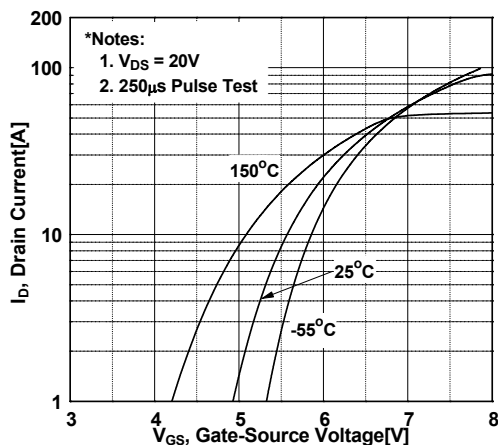


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

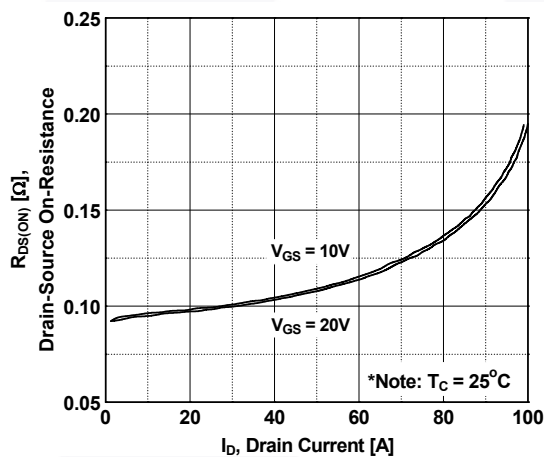


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

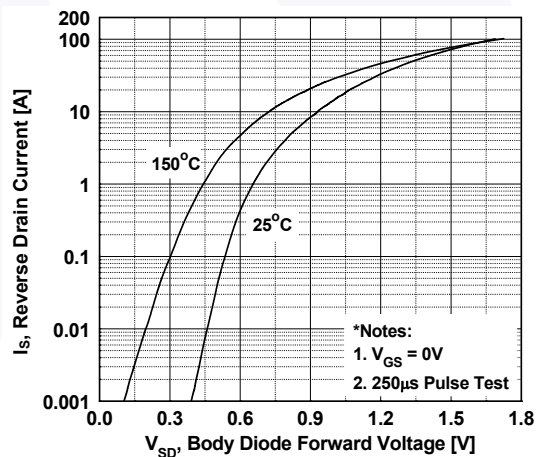


Figure 5. Capacitance Characteristics

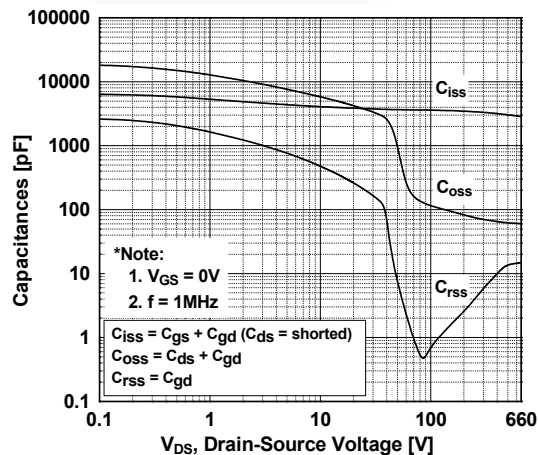
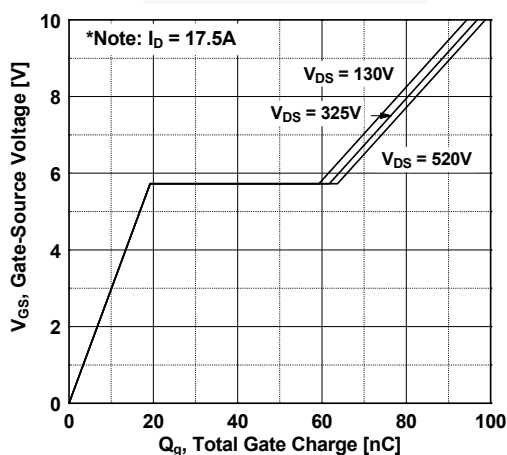


Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

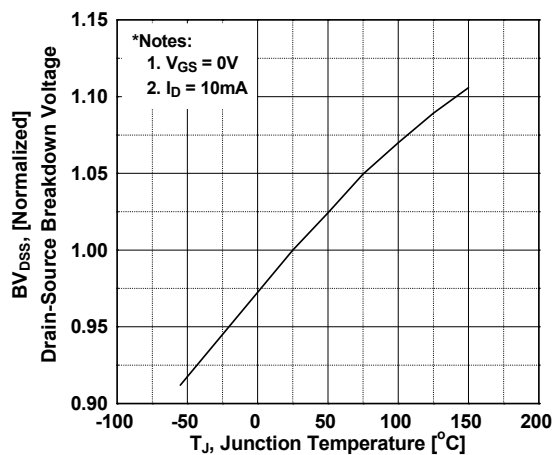


Figure 8. On-Resistance Variation vs. Temperature

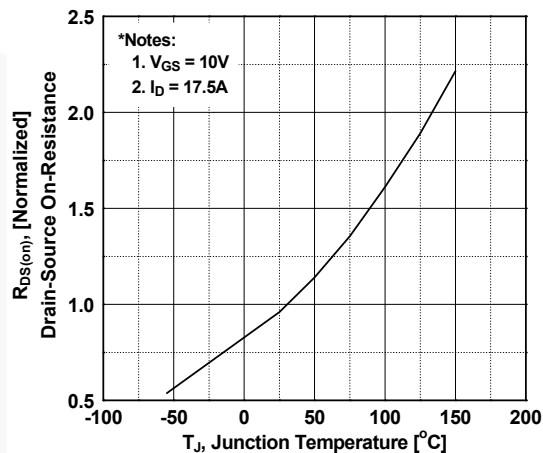


Figure 9. Maximum Safe Operating Area

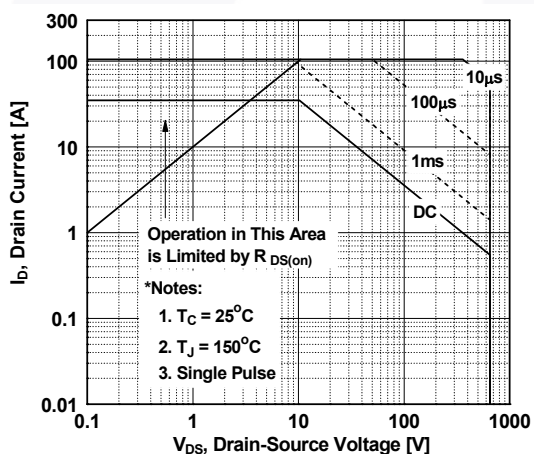


Figure 10. Maximum Drain Current vs. Case Temperature

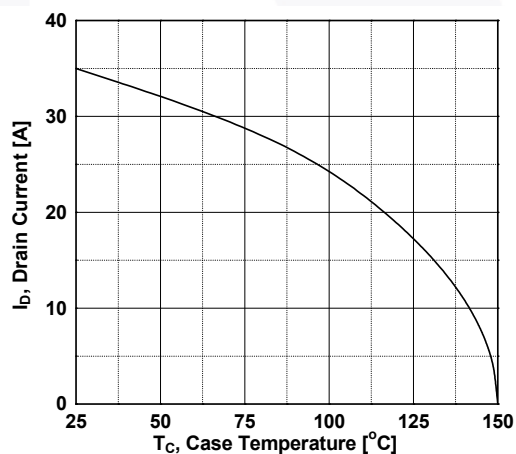
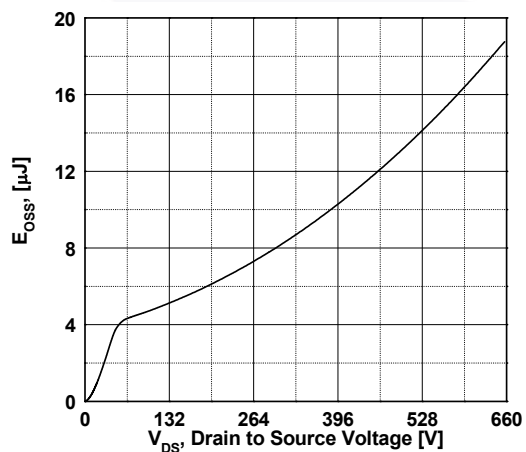
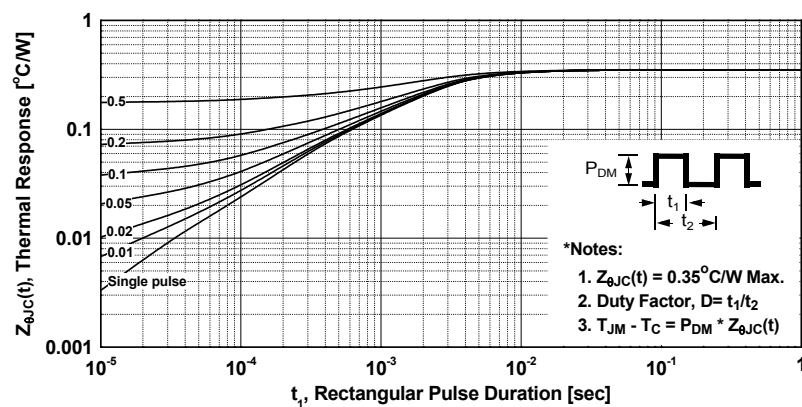


Figure 11. E<sub>oss</sub> vs. Drain to Source Voltage Switching Capability



# Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



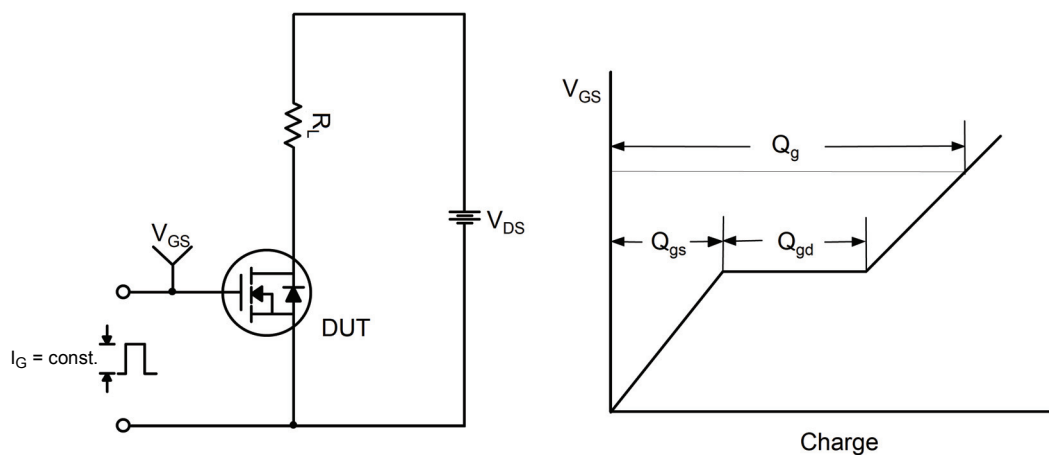


Figure 13. Gate Charge Test Circuit & Waveform

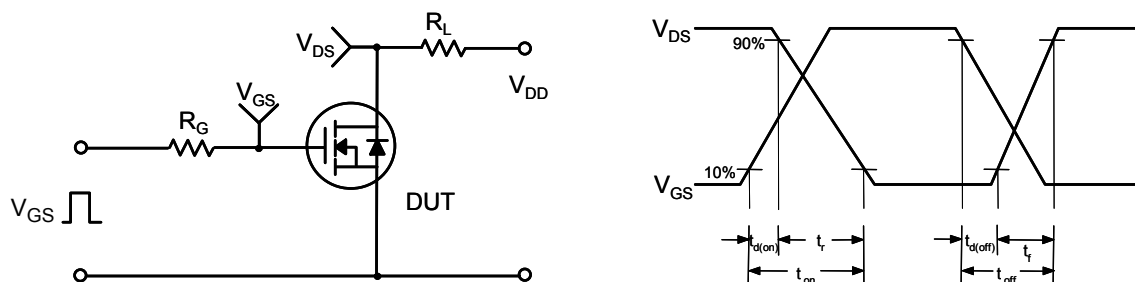


Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

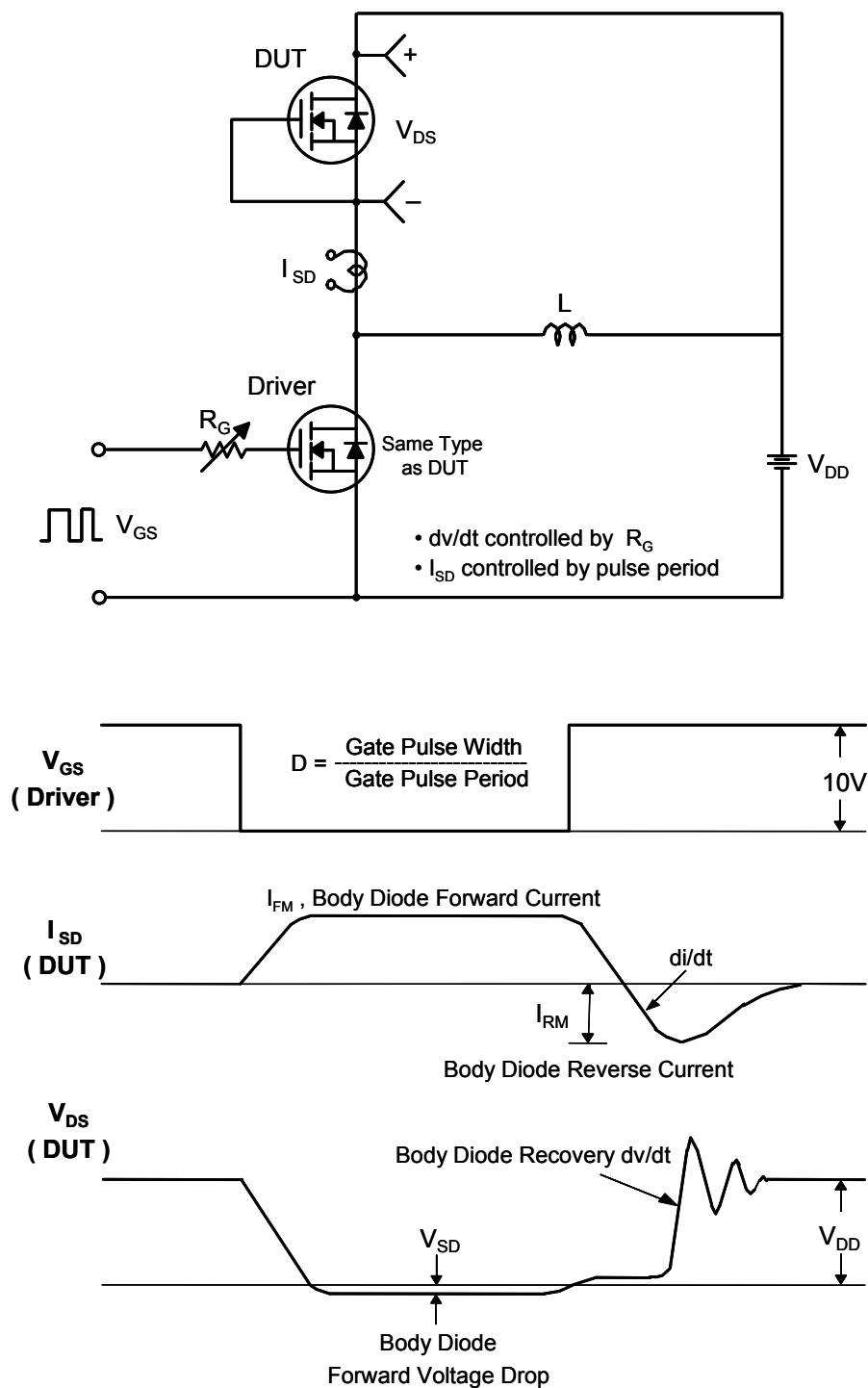
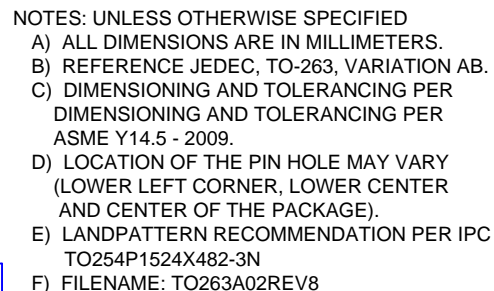
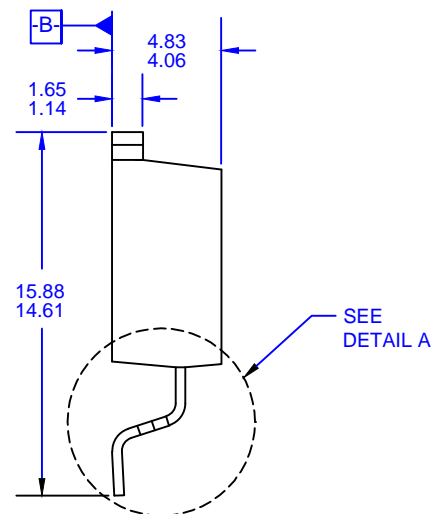
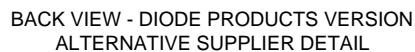
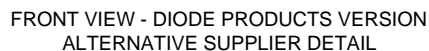


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms





ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada

**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative